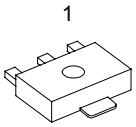
UTC 2SC3468 NPN EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR FOR
VIDEO OUTPUT OF HIGH-DEFINITION
CRT DISPLAYS



SOT-89

1: BASE 2: COLLECTOR 3: EMITTER

*Pb-free plating product number: 2SC3468L

FEATURES

* High breakdown voltage: V_{CBO}, $V_{CEO} \geqq 300V$
* Small reverse transfer capacitance and excellent high frequency characteristicF

ABSOLUTE MAXIMUM RATINGS (Ta = 25℃)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-to-Base Voltage	V_{CBO}	300	V
Collector-to-Emitter Voltage	V_{CEO}	300	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Current (Pulse)	I_{CP}	200	mA
Collector Dissipation	P_C	1.0	W
Junction Temperature	T_J	0 ~ +125	℃
Storage Temperature	T_{STG}	-65 ~ +125	℃

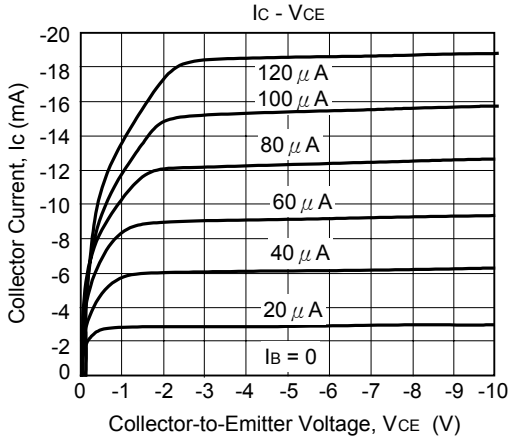
ELECTRICAL CHARACTERISTICS (Ta = 25℃)

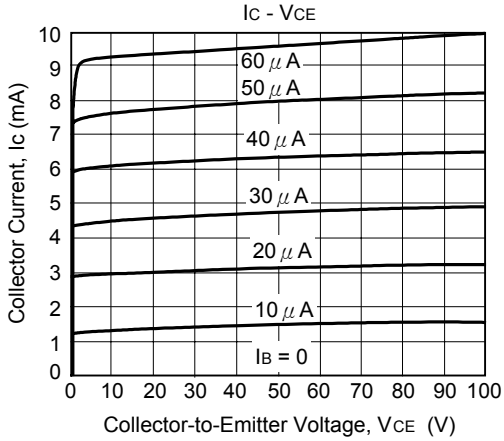
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I_{CBO}	V_{CB} = 200V, I_E = 0			0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0			0.1	μA
DC Current Gain	h_{FE}	V_{CE} = 10V, I_C = 10mA	40		320	
Gain-Bandwidth Product	f_T	V_{CE} = 30V, I_C = 10mA		150		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE\ (sat)}$	I_C = 20mA, I_B = 2mA			0.6	V
Base-to-Emitter Saturation Voltage	$V_{BE\ (sat)}$	I_C = 20mA, I_B = 2mA			1.0	V
Collector-to-Base Breakdown Voltage	$V_{(BR)\ CBO}$	I_C = 10μA, I_E = 0	300			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)\ CEO}$	I_C = 1mA, R_{BE} = ∞	300			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)\ EBO}$	I_E = 10μA, I_C = 0	5			V
Output Capacitance	Cob	V_{CB} = 30V, f = 1MHz		2.6		pF
Reverse Transfer Capacitance	Cre	V_{CB} = 30V, f = 1MHz		1.8		pF

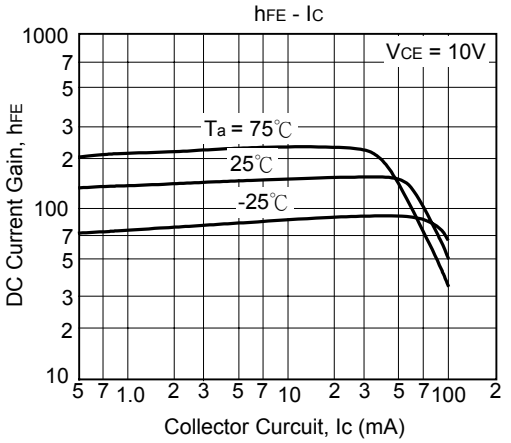
CLASSIFICATION of h_{FE}

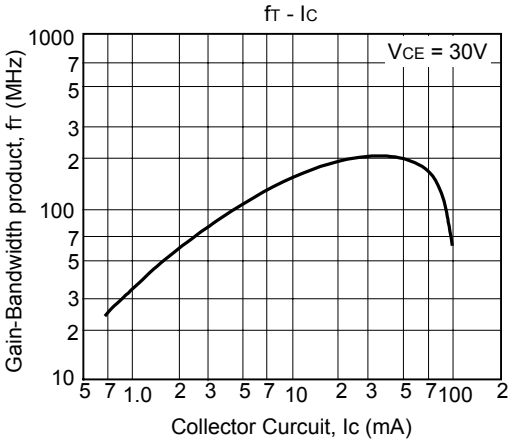
RANK	C	D	E	F
RANGE	40 ~ 80	60 ~ 120	100 ~ 200	160 ~ 320

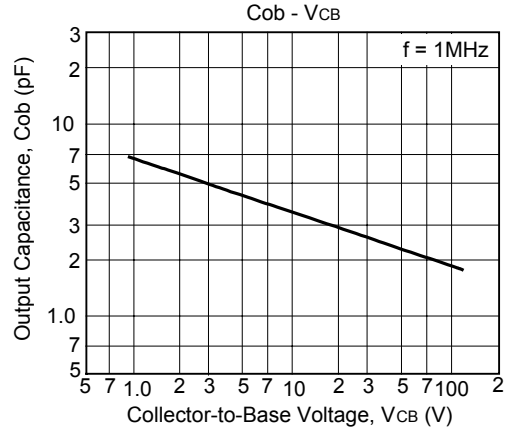
TYPICAL CHARACTERS

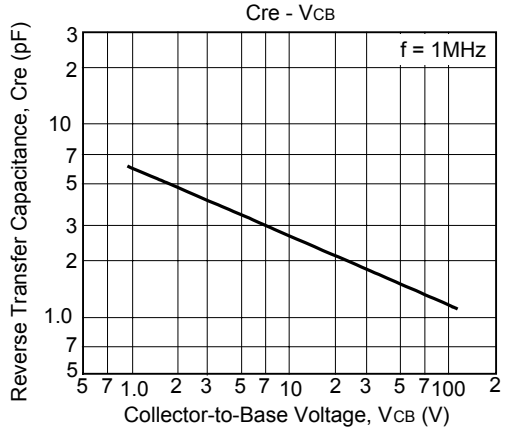




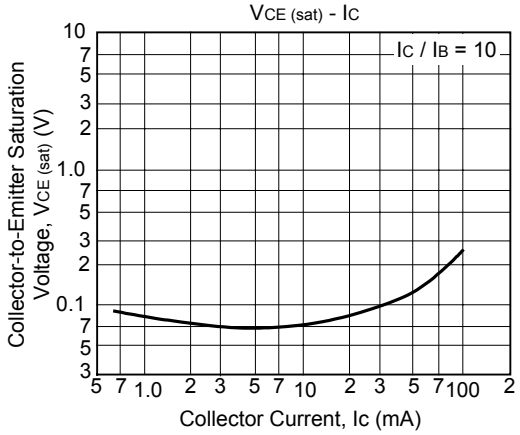




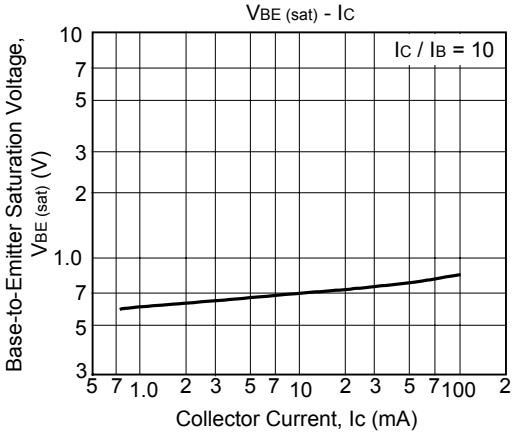




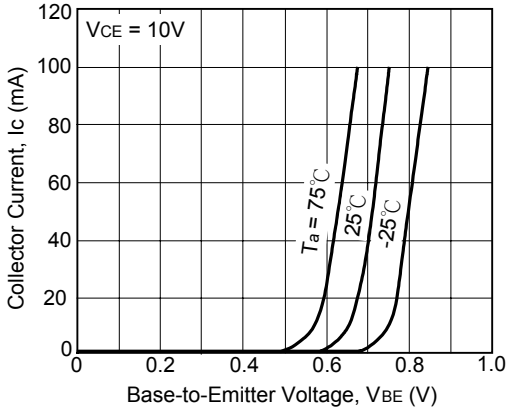
$V_{CE\ (sat)}$ - I_C



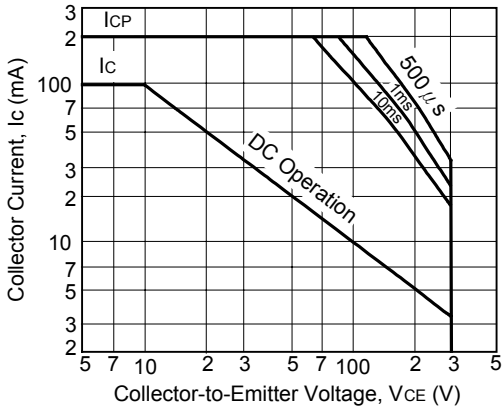
$V_{BE\ (sat)}$ - I_C



I_C - V_{BE}



A S O



Pc - Ta